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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
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| 09/440,595 | 11/15/1999 | NAVEED MAJID | PHA-23843 | 3147 |
| | 7590 09/25/2002 | | | |
| CORPORATE PATENT COUNSEL US PHILIPS CORPORATION 580 WHITE PLAINS ROAD | | | EXAMINER | |
| | | | PAREKH, NITIN | |
| | N, NY 10591 | | ART UNIT | PAPER NUMBER |
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| | | | 2811 | |
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Please find below and/or attached an Office communication concerning this application or proceeding.



Application No. 09/440,595

Applicant(s)

Examiner

Nitin Parekh

Art Unit

Majid et al

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Office Action Summary

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

| A SHOTHE No. Extens mailing. If the point of NO. Failure. Any re | date of this communication. Deriod for reply specified above is less than thirty (30) days, a reply within the period for reply is specified above, the maximum statutory period will apply to reply within the set or extended period for reply will, by statute, cause the ply received by the Office later than three months after the mailing date of the ply received by the Office later than three months after the mailing date. | no event, however, may a reply be timely filed after SIX (6) MONTHS from the statutory minimum of thirty (30) days will be considered timely. and will expire SIX (6) MONTHS from the mailing date of this communication. he application to become ABANDONED (35 U.S.C. § 133). | | |
|--|--|---|--|--|
| | patent term adjustment. See 37 CFR 1.704(b). | | | |
| Status 1) 💢 | Responsive to communication(s) filed on Jul 2, 20 | 12 | | |
| 2a) 🔲 | This action is FINAL . 2b) ★ This act | | | |
| 3) 🗆 | • | except for formal matters, prosecution as to the merits is | | |
| Disposit | tion of Claims | ne dudyle, 1959 C.D. 11, 455 O.G. 215. | | |
| | | is/are pending in the application. | | |
| | | is/are withdrawn from consideration. | | |
| | Claim(s) | | | |
| 6) 🔀 | Claim(s) <u>1-7</u> | | | |
| _ | Claim(s) | | | |
| | | are subject to restriction and/or election requirement. | | |
| | tion Papers | | | |
| | The specification is objected to by the Examiner. | | | |
| 10) | | a) accepted or b) objected to by the Examiner. | | |
| | Applicant may not request that any objection to the d | | | |
| 11) | | is: a) □ approved b) □ disapproved by the Examiner | | |
| | If approved, corrected drawings are required in reply | to this Office action. | | |
| 12) | The oath or declaration is objected to by the Exami | ner. | | |
| Priority | under 35 U.S.C. §§ 119 and 120 | , | | |
| 13)□ | Acknowledgement is made of a claim for foreign p | riority under 35 U.S.C. § 119(a)-(d) or (f). | | |
| a) |] All b)□ Some* c)□ None of: | | | |
| • | 1. \square Certified copies of the priority documents hav | e been received. | | |
| 2 | 2. \square Certified copies of the priority documents hav | e been received in Application No | | |
| ; | 3. Copies of the certified copies of the priority de application from the International Bure | ocuments have been received in this National Stage au (PCT Rule 17.2(a)). | | |
| *Se | ee the attached detailed Office action for a list of the | e certified copies not received. | | |
| 14) | Acknowledgement is made of a claim for domestic | priority under 35 U.S.C. § 119(e). | | |
| a) [_ | and the second s | | | |
| 15)∟ | Acknowledgement is made of a claim for domestic | priority under 35 U.S.C. §§ 120 and/or 121. | | |
| Attachme | | | | |
| | ice of References Cited (PTO-892) | 4) Interview Summary (PTO-413) Paper No(s). | | |
| | cice of Draftsperson's Patent Drawing Review (PTO-948) promotion Disclosure Statement(s) (PTO-1449) Paper No(s), 4 and ; | 5) Notice of Informal Patent Application (PTO-152) | | |
| 21 XI IIII | America disclosure Statement(s) (P10-1449) Paper No(s), 7 010 | 6) Other: | | |

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Uchida et al (US Pat. 6060748) in view of Oka et al (6140690), Takagi et al (US Pat. 6130458) and Lauffer et al (IDS-paper #4, European Pat. 0471938A1).

Regarding claim 1, Uchida et al disclose a multichip integrate circuit (IC) module (MCM)/device comprising:

-a high power semiconductor device (130, 130a and 130b in Fig. 1) such as MOS type field effect transistor (FET), bipolar transistor, etc. formed on a silicon-0n-insulator (SOI) substrate region (100 in Fig. 1; Col. 4, line 45- Col. 5, line 5) and a low power/low speed device (140 and 140a in Fig. 1) such as a transistor (Col. 5) formed on a silicon/bulk technology substrate region (120 in Fig. 1; Col. 5, line 16), and

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a substrate (100/110/120, 200, 210, 11, etc. in Fig. 1-3)

(Fig. 1-3; Col. 4, line 45-Col. 7, line 10).

Uchida et al fail to specify the low power device/chip being a control chip and the power chip and control chip being directly mounted on the electrically conductive heat sink connected to ground potential.

Oka et al teach using a MCM where a power device (50 in Fig. 4 and 5) having a high voltage/current is disposed on a common substrate with a weak/low signal device (60 in Fig. 5) functioning as a control and a sensor device (Col. 2, line 15-25; Col. 5; Col. 17).

Lauffer et al teach using a multichip module having a variety of chips such as high power, low power, memory, logic chip, etc. comprising a bulk/conventional technology device and SOI device being directly mounted on the electrically conductive heat sink/substrate made of copper (11 in Fig. 4; Col. 9, line 7) which is connected to a ground potential (Col. 12, line 32).

Takagi et al teach using a multichip hybrid integrate circuit (IC)/module comprising a high/low level power semiconductor chips (200 in Fig. 12A and B) and respective high/low level control semiconductor chips (100 in Fig. 12A and B) devices

being directly mounted on an electrically conductive substrate connected to ground potential (81 in Fig. 12B; Col. 11, line 30-Col. 12, line 57).

The cited reference by Hill (US Pat. 6028348, Fig. 3; Col. 2, line 66) teach using a multichip module with the chips mounted on a conventional metal/electrically conductive substrate which serves as a heat sink.

Therefore, it would have been obvious to a person of ordinary skill in the art at the time invention was made to incorporate a MCM having a power chip and a control chip being directly mounted on an electrically conductive heat sink substrate connected to ground potential so that heat dissipation and temperature distribution can be improved using Oka et al, Lauffer et al and Takagi et al's chip/substrate structures in Uchida et al's multichip module.

Regarding claims 2-4, Uchida et al fail to specify the control chip comprising BIMOS, CMOS or bipolar device.

Takagi et al disclose the control semiconductor chips comprising CMOS or any other conventional configurations comprising BICMOS, bipolar, n-MOS, etc. (Col. 13, line 64).

Therefore, it would have been obvious to a person of ordinary skill in the art at the time invention was made to incorporate a control chip comprising BIMOS, CMOS or bipolar device so that the current handling/breakdown voltage capability can be

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improved Oka et al, Lauffer et al and Takagi et al's chip/substrate structures in Uchida

et al's multichip module.

Regarding claims 5-7, the claim elements have been addressed as explained above in

the rejection for claim 1.

Response to Arguments

2. Applicant's arguments with respect to claims 1-7 have been considered but are

moot in view of the new ground(s) of rejection.

Papers related to this application may be submitted directly to Art Unit 2811 by

facsimile transmission. Papers should be faxed to Art Unit via Technology Center 2800

fax center located in Crystal Plaza 4, room 4C23. The faxing of such papers must

conform with the notice published in the Official Gazette, 1096 OG 30 (15 November

1989).

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Nitin Parekh whose telephone number in (703) 305-

3410. The examiner can be normally reached on Monday-Friday from 08:30 am-5:00

pm.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas, can be reached on (703) 308-2772. The fax number for the organization where this application or proceeding is assigned is (703) 308-7722 or 7724.

Nitin Parekh

09-12-02

Steven Loke